



(11) **EP 2 394 299 B8**

(12) **CORRECTED EUROPEAN PATENT SPECIFICATION**

(15) Correction information:
Corrected version no 1 (W1 B1)
Corrections, see
Bibliography INID code(s) 73

(48) Corrigendum issued on:
25.01.2017 Bulletin 2017/04

(45) Date of publication and mention
of the grant of the patent:
23.11.2016 Bulletin 2016/47

(21) Application number: **09786348.4**

(22) Date of filing: **03.02.2009**

(51) Int Cl.:
H01L 29/417 ^(2006.01) **H01L 29/51** ^(2006.01)
H01L 29/66 ^(2006.01) **H01L 29/778** ^(2006.01)
H01L 29/872 ^(2006.01) **H01L 29/20** ^(2006.01)
H01L 21/74 ^(2006.01) **H01L 27/06** ^(2006.01)
H01L 29/08 ^(2006.01)

(86) International application number:
PCT/IB2009/051306

(87) International publication number:
WO 2010/089632 (12.08.2010 Gazette 2010/32)

(54) **SEMICONDUCTOR STRUCTURE AND A METHOD FOR MANUFACTURING A SEMICONDUCTOR STRUCTURE**

HALBLEITERSTRUKTUR UND VERFAHREN ZUM HERSTELLEN EINER HALBLEITERSTRUKTUR
STRUCTURE SEMI-CONDUCTRICE ET PROCÉDÉ DE FABRICATION D'UNE TELLE STRUCTURE

(84) Designated Contracting States:
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR
HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL
PT RO SE SI SK TR

(43) Date of publication of application:
14.12.2011 Bulletin 2011/50

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US-A1- 2007 045 765

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